[TS05W2]

Angstrom-Scale 2D Materials for Beyond-Nano Technology 2

Date & Time	July 8(Wed.), 2026 / 15:50–17:50
Place	Room 304
Session Chair(s)	Prof. Kibum Kang (KAIST)

TS05W2_I_1 ***Invited** 15:50–16:20

Towards the Development of Wafer-Scale Integration Using 2D Materials

Kosuke Nagashio

(The University of Tokyo)

TS05W2_I_2 ***Invited** 16:20–16:50

Sliding Ferroelectricity in Wafer-Scale Single-Crystal 2D Materials

Gwan-Hyoung Lee

(Seoul National University)

TS05W2_O_3 ***YSA Applied** 16:50–17:05

Phase Controlled Growth of Single Crystal Multilayer Transition Metal Dichalcogenides

Taejoon Mo[1,2], Gunwoo yoo[1,2], Dong-yeong Kim[1,2], Yosub Choi[1,2], and Cheol-joo Kim[1,2]

([1]Institute for Basic Science, [2]Pohang University of Science and Technology)

TS05W2_O_4 ***YSA Applied** 17:05–17:20

Engineering 2D Janus Materials: Deterministic Conversion of $PtSe_2$ to Janus PtSSe and PtS_2 via Temperature-Controlled Remote Plasma Treatment

Dong-Hyun Kim[1,2], Byung Joon Moon[1], Minseung Gyeon[3], Yuseok Kim[3], Jinwoo Kim[4], Dongchul Sung[5], Minji Park[1,6], Daekwon Lee[7], Sooyeon Ra[1,7], Gillian Nolan[8], Han-Koo Lee[9], Min Ji Im[1], Unseok Jung[1], Yunjo Jeong[10], Changheon Kim[1,4], Jimin Jang[4], Seok-ki Hyeong[1], Taesung Kim[2], Sang Kyu Park[1], Sangmin An[7], Jaehyung Yu[11], Hunsu Lee[1], Suklyun Hong[5], Pinshane Y. Huang[8], Sanghan Lee[6], Gwan-Hyoung Lee[4], Kibum Kang[3], Heesuk Rho[7], Sukang Bae[1], Changgu Lee[2], and Jangyup Son[1,12]

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TS05W2_O_6 17:20–17:35

Localizing Electrochemistry in 2D Materials Junction

Yin-Zhi Weng[1,2], Radha Raman[1,2], Ding-Rui Chen[1,2], Ya-Ping Hsieh[1], and Mario Hofmann[2]

([1]Institute of Atomic and Molecular Sciences, [2]National Taiwan University)

TS05W2_O_7 ***YSA Applied** 17:35–17:50

Van der Waals Epitaxial InSe Thin Films for High-Mobility Field-Effect Transistors

Imhwan Kim[1], Yoonkang Kim[1], Winwood Suh[1], Eunsu Lee[1], Hyunjun Jo[3], Kyusun Han[2], Myeongju Kim[1], Joohee Oh[1], Joonyoung Park[5], Hong Seok Oh[2], Hyeonjun Baek[3], Celesta S. Chang[1], Kyusang Lee[4], Chul-Ho Lee[1], and Gyu-Chul Yi[1]

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